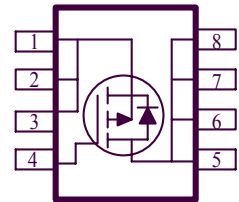
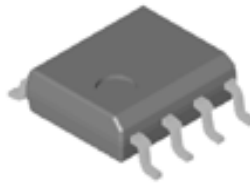


## P-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low  $r_{DS(on)}$  assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

- Low  $r_{DS(on)}$  Provides Higher Efficiency and Extends Battery Life
- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Extended VGS range ( $\pm 25$ ) for battery pack applications



PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ m( $\Omega$ )	$I_D$ (A)
-30	30 @ $V_{GS} = -10V$	9.5
	52 @ $V_{GS} = -4.5V$	7.5

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		$V_{DS}$	-30	V
Gate-Source Voltage		$V_{GS}$	$\pm 25$	
Continuous Drain Current <sup>a</sup>	$T_A = 25^\circ\text{C}$	$I_D$	9.5	A
	$T_A = 70^\circ\text{C}$		8.3	
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	$\pm 50$	
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	-2.1	A
Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	$P_D$	3.1	W
	$T_A = 70^\circ\text{C}$		2.6	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Case <sup>a</sup>	$t \leq 5$ sec	$R_{\theta JC}$	25	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ sec	$R_{\theta JA}$	50	$^\circ\text{C}/\text{W}$

#### Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

SPECIFICATIONS ( $T_A = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1	-1.6	-3	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			-5	
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-50			A
Drain-Source On-Resistance <sup>A</sup>	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -9.5\text{ A}$		24	30	m $\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -7.5\text{ A}$		44	52	
		$V_{GS} = -10\text{ V}, I_D = -9.5\text{ A}, T_J = 55^\circ\text{C}$		29	36	
Forward Transconductance <sup>A</sup>	$g_{fs}$	$V_{DS} = -15\text{ V}, I_D = -9.5\text{ A}$		31		S
Diode Forward Voltage	$V_{SD}$	$I_S = -2.1\text{ A}, V_{GS} = 0\text{ V}$		-0.7	-1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V},$ $I_D = -9.5\text{ A}$		15	26	nC
Gate-Source Charge	$Q_{gs}$			5.8		
Gate-Drain Charge	$Q_{gd}$			12		
<b>Switching</b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega, I_D = -1\text{ A},$ $V_{GEN} = -10\text{ V}, R_G = 6\text{ }\Omega$		15	26	nS
Rise Time	$t_r$			12	21	
Turn-Off Delay Time	$t_{d(off)}$			62	108	
Fall-Time	$t_f$			46	71	

## Notes

- Pulse test:  $PW \leq 300\mu\text{s}$  duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.

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## Typical Electrical Characteristics (P-Channel)

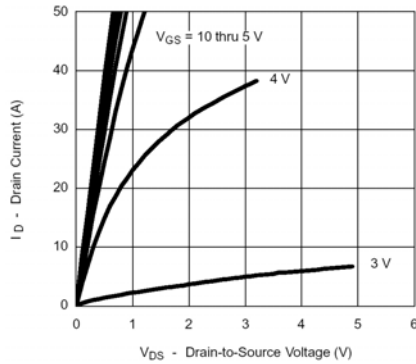


Figure 1. On-Region Characteristics

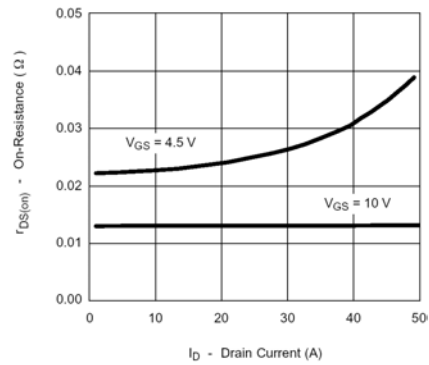


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

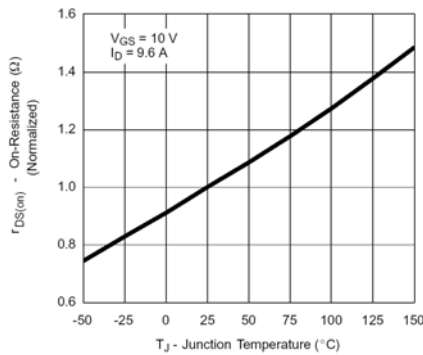


Figure 3. On-Resistance Variation with Temperature

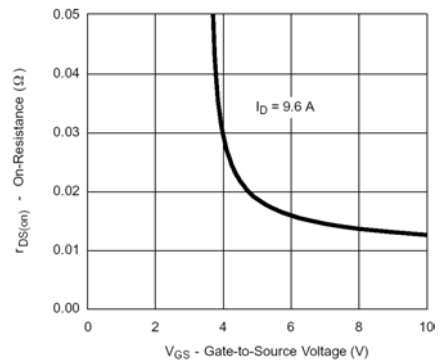


Figure 4. On-Resistance Variation with Gate to Source Voltage

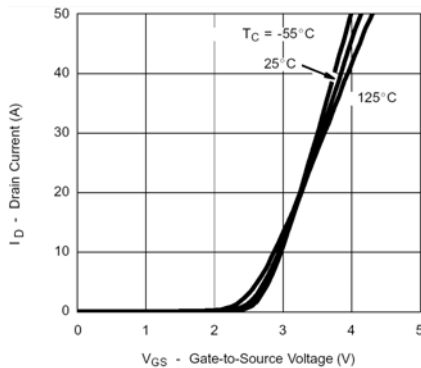


Figure 5. Transfer Characteristics

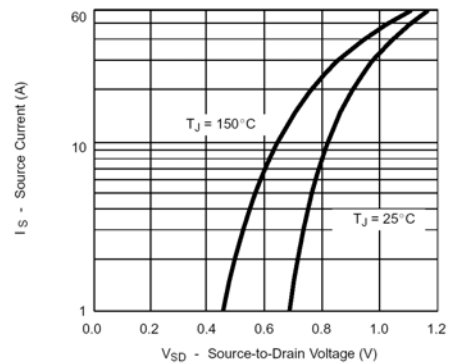


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

## Typical Electrical Characteristics (P-Channel)

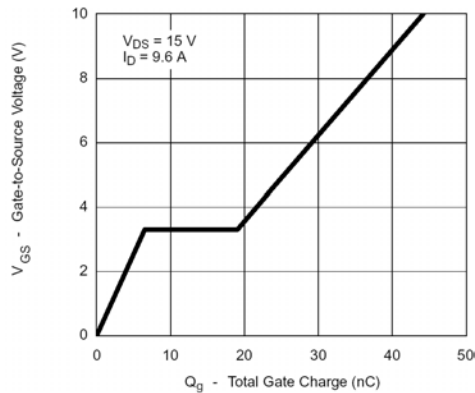


Figure 7. Gate Charge Characteristics

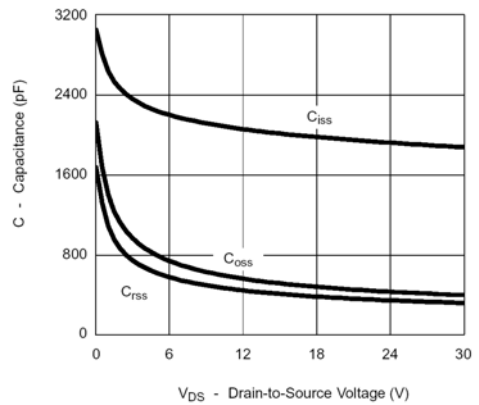


Figure 8. Capacitance Characteristics

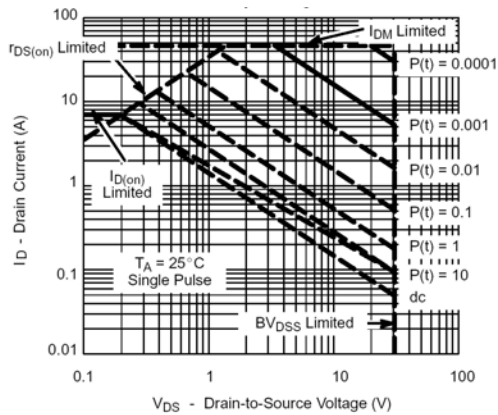


Figure 9. Maximum Safe Operating Area

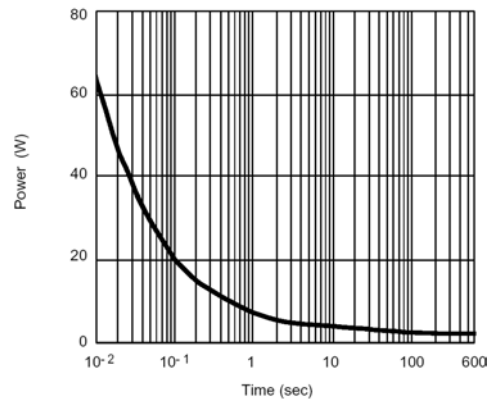


Figure 10. Single Pulse Maximum Power Dissipation

### Normalized Thermal Transient Junction to Ambient

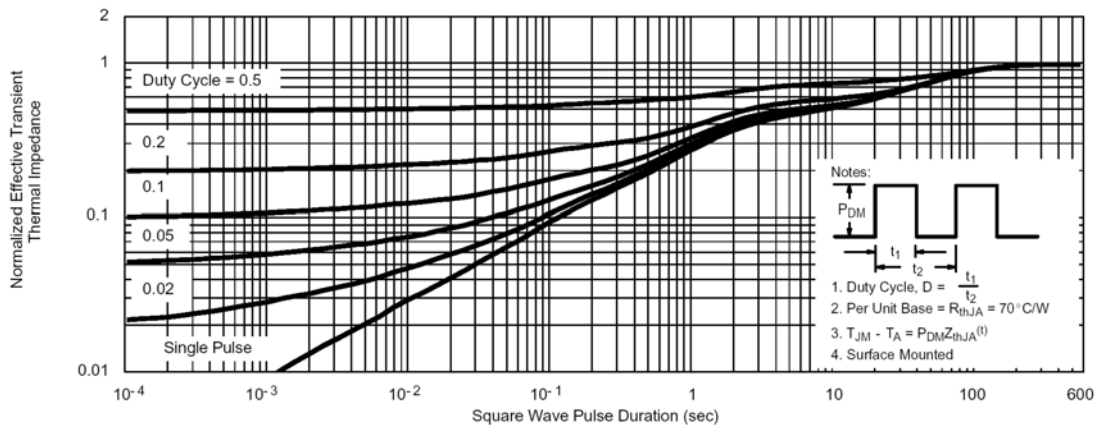
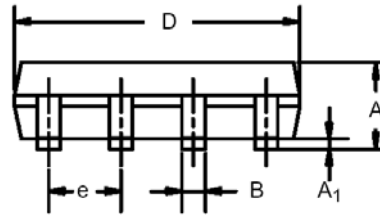
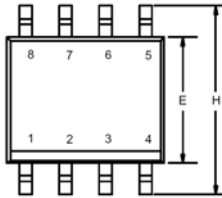


Figure 11. Transient Thermal Response Curve

Package Information

SO-8: 8LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

